N-Channel 150-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

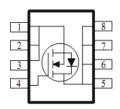
| PRODUCT SUMMARY | | | |
|---------------------|-----------------------------|--------------------|--|
| V _{DS} (V) | $r_{DS(on)}(m\Omega)$ | I _D (A) | |
| 150 | 48 @ V _{GS} = 10V | 8.3 | |
| 130 | 54 @ V _{GS} = 5.5V | 7.9 | |



FREE



DFN5X6-8L



| ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED) | | | | | | | |
|---|----------------------|-------------------|------------|----|--|--|--|
| Parameter | Symbol | Limit | Units | | | | |
| Drain-Source Voltage | V_{DS} | 150 | V | | | | |
| Gate-Source Voltage | | V_{GS} | ±20 | V | | | |
| Continuous Drain Current a | T _A =25°C | 1 | 8.3 | | | | |
| Continuous Drain Current | T _A =70°C | l _D | 6.7 | Α | | | |
| Pulsed Drain Current ^b | | I _{DM} | 50 | | | | |
| Continuous Source Current (Diode Conduction) a | | I _S | 7.1 | Α | | | |
| Power Dissipation ^a | T _A =25°C | P _D | 5 | W | | | |
| Power Dissipation | T _A =70°C | ' D | 3.2 | VV | | | |
| Operating Junction and Storage Temperature Range | | T_J , T_{stg} | -55 to 150 | °C | | | |

| THERMAL RESISTANCE RATINGS | | | | | | | |
|--|--------------|-----------------|-------|------|--|--|--|
| Parameter | Symbol | Maximum | Units | | | | |
| Maximum Junction-to-Ambient ^a | t <= 10 sec | $R_{\theta JA}$ | 25 | °C/W | | | |
| Maximum Junction-to-Ambient | Steady State | | 65 | C/VV | | | |

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

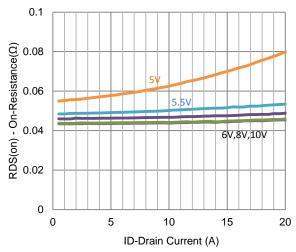
| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit | |
|---------------------------------|---------------------|---|-----|------|------|-------|--|
| Static | | | | | | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$ | 1 | | | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ±100 | nA | |
| Zero Gate Voltage Drain Current | lass | $V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$ | | | 1 uA | | |
| Zero Gate Voltage Brain Gurrent | I _{DSS} | $V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ | | | 25 | uA | |
| On-State Drain Current | I _{D(on)} | $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 15 | | | Α | |
| Drain-Source On-Resistance | r | $V_{GS} = 10 \text{ V}, I_D = 8.3 \text{ A}$ | 48 | | 48 | mΩ | |
| Dialii-30dice Oil-Resistance | r _{DS(on)} | $V_{GS} = 5.5 \text{ V}, I_D = 6.4 \text{ A}$ | | | 54 | 11152 | |
| Forward Transconductance | g _{fs} | $V_{DS} = 15 \text{ V}, I_{D} = 8.3 \text{ A}$ | | 15 | | S | |
| Diode Forward Voltage | V_{SD} | $I_S = 3.6 \text{ A}, V_{GS} = 0 \text{ V}$ | | 0.74 | | V | |
| | | Dynamic | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 75 \text{ V}, V_{GS} = 5.5 \text{ V},$ | | 58 | | | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = 73 \text{ V}, V_{GS} = 3.3 \text{ V},$ $I_{D} = 8.3 \text{ A}$ | | 17 | | nC | |
| Gate-Drain Charge | Q_gd | 1 _D = 0.5 A | | 35 | | | |
| Turn-On Delay Time | t _{d(on)} | $V_{DS} = 75 \text{ V}, R_1 = 9.1 \Omega,$ | | 20 | | | |
| Rise Time | t _r | $V_{DS} = 73 \text{ V}, \text{ N}_{L} = 9.1 \Omega_{2},$ $I_{D} = 8.3 \text{ A},$ | | 35 | | ne | |
| Turn-Off Delay Time | $t_{d(off)}$ | $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$ | | 122 | | ns | |
| Fall Time | t_f | v _{GEN} = 10 v, r(_{GEN} = 0.22 | | 38 | | | |
| Input Capacitance | C _{iss} | | | 4388 | | | |
| Output Capacitance | C _{oss} | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 260 | | pF | |
| Reverse Transfer Capacitance | C_{rss} | | | 239 | | | |

Notes

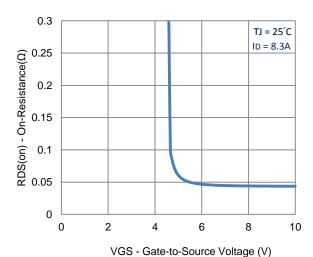
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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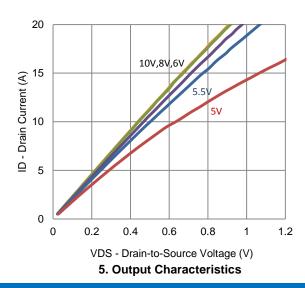
Typical Electrical Characteristics

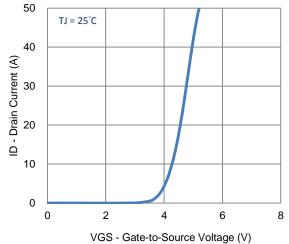


1. On-Resistance vs. Drain Current

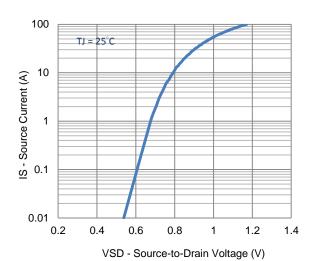


3. On-Resistance vs. Gate-to-Source Voltage

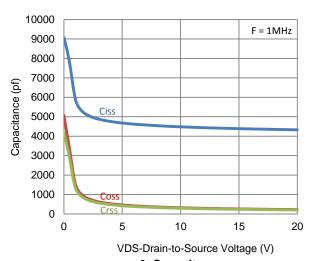




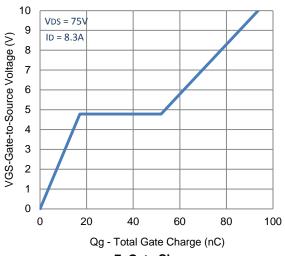
2. Transfer Characteristics

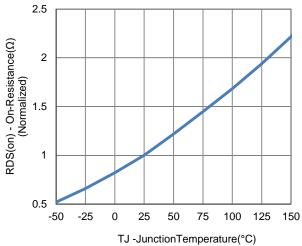


4. Drain-to-Source Forward Voltage



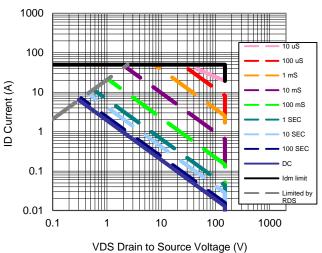
Typical Electrical Characteristics

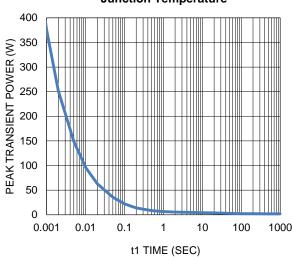




7. Gate Charge

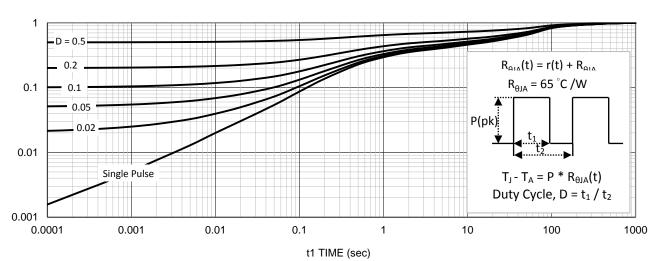






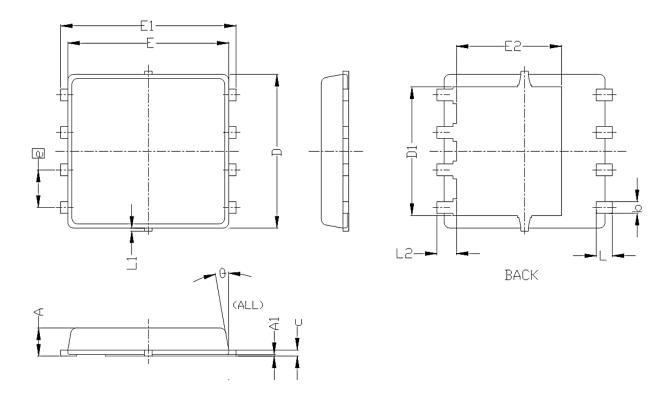
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



| SYMBOLS | DIMENSIONS IN MILLIMETERS | | DIMENSIONS IN INCHES | | | | |
|---------|---------------------------|-------|----------------------|------------|-------|-------|--|
| STMBULS | MIN | NOM | MAX | MIN | NOM | MAX | |
| A | 0.85 | 0.95 | 1.00 | 0.033 | 0.037 | 0.039 | |
| Al | 0.00 | | 0.05 | 0.000 | | 0.002 | |
| b | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 | |
| С | 0. 15 | 0. 20 | 0. 25 | 0.006 | 0.008 | 0.010 | |
| D | 5, 20 BSC | | | 0. 205 BSC | | | |
| D1 | 4. 35 BSC | | | 0. 171 BSC | | | |
| | | | | | | | |
| Е | 5, 55 BSC | | | 0, 219 BSC | | | |
| E1 | 6. 05 BSC | | 0. 238 BSC | | | | |
| E2 | 3. 62 BSC | | 0. 143 BSC | | | | |
| e | 1. 27 BSC | | | 0.050 BSC | | | |
| L | 0.45 | 0.55 | 0.65 | 0.018 | 0.022 | 0.026 | |
| L1 | 0 | | 0.15 | 0 | | 0.006 | |
| L2 | 0.68 REF | | | 0.027 REF | | | |
| θ | 0° | | 10° | 0° | | 10° | |